SKKT 280, SKKH 280

THYRISTOR BRIDGE,SCR,BRIDGE

SEMIPACK® 3 new

Thyristor / Diode Modules

SKKH 280

SKKT 280

Features

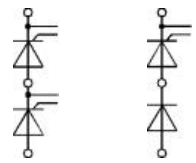
- Heat transfer through aluminium nitride ceramic isolated metal baseplate
- Precious metal pressure contacts for high reliability
- Thyristor with amplifying gate
- UL recognized, file no. E 63 532

Typical Applications

- DC motor control (e. g. for machine tools)
- AC motor starters
- Temperature control (e. g. for ovens, chemical processes)
- Professional light dimming (studios, theaters)

1) See the assembly instructions

2) The screws must be lubricated



SKKT **SKKH**

V_{RSM} V	V_{RRM}, V_{DRM} V	I_{TRMS} = 440 A (maximum value for continuous operation) I_{TAV} = 280 A (sin. 180; T_c = 79 °C)		
2100	2000	SKKT 280/20E H4	SKKH 280/20E H4	
2300	2200	SKKT 280/22E H4	SKKH 280/22E H4	

Symbol	Conditions	Values	Units
I_{TAV}	sin. 180; T_c = 79 (85) °C;	280 (252)	A
I_{TSM}	T_{vj} = 25 °C; 10 ms	8500	A
	T_{vj} = 125 °C; 10 ms	7500	A
i²t	T_{vj} = 25 °C; 8,3 ... 10 ms	361000	A²s
	T_{vj} = 125 °C; 8,3 ... 10 ms	281000	A²s
V_T	T_{vj} = 25 °C; I_T = 750 A	max. 1,55	V
$V_{T(TO)}$	T_{vj} = 125 °C	max. 0,9	V
r_T	T_{vj} = 125 °C	max. 0,75	mΩ
I_{DD}; I_{RD}	T_{vj} = 125 °C; V_{RD} = V_{RRM}; V_{DD} = V_{DRM}	max. 60	mA
t_{gd}	T_{vj} = 25 °C; I_G = 1 A; di_G/dt = 1 A/µs	1	µs
t_{gr}	V_D = 0,67 * V_{DRM}	2	µs
$(di/dt)_{cr}$	T_{vj} = 125 °C	max. 250	A/µs
$(dv/dt)_{cr}$	T_{vj} = 125 °C	max. 1000	V/µs
t_q	T_{vj} = 125 °C ,	50 ... 150	µs
I_H	T_{vj} = 25 °C; typ. / max.	150 / 500	mA
I_L	T_{vj} = 25 °C; R_G = 33 Ω; typ. / max.	300 / 2000	mA
V_{GT}	T_{vj} = 25 °C; d.c.	min. 3	V
I_{GT}	T_{vj} = 25 °C; d.c.	min. 200	mA
V_{GD}	T_{vj} = 125 °C; d.c.	max. 0,25	V
I_{GD}	T_{vj} = 125 °C; d.c.	max. 10	mA
$R_{th(j-c)}$	cont.; per thyristor / per module	0,11 / 0,055	K/W
$R_{th(j-c)}$	sin. 180; per thyristor / per module	0,116 / 0,058	K/W
$R_{th(j-c)}$	rec. 120; per thyristor / per module	0,13 / 0,065	K/W
$R_{th(c-s)}$	per thyristor / per module	0,04 / 0,02	K/W
T_{vj}		- 40 ... + 125	°C
T_{stg}		- 40 ... + 125	°C
V_{isol}	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	4800 / 4000	V~
M_s	to heatsink	9 ± 15 %[1)]	Nm
M_t	to terminal	9 ± 15 %[2)]	Nm
a		5 * 9,81	m/s²
m	approx.	600	g
Case	SKKT	A 73b	
	SKKH	A 76b	

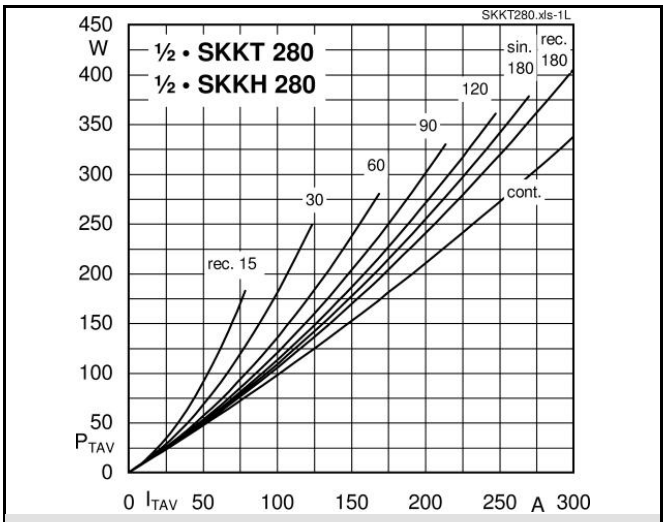


Fig. 1L Power dissipation per thyristor vs. on-state current

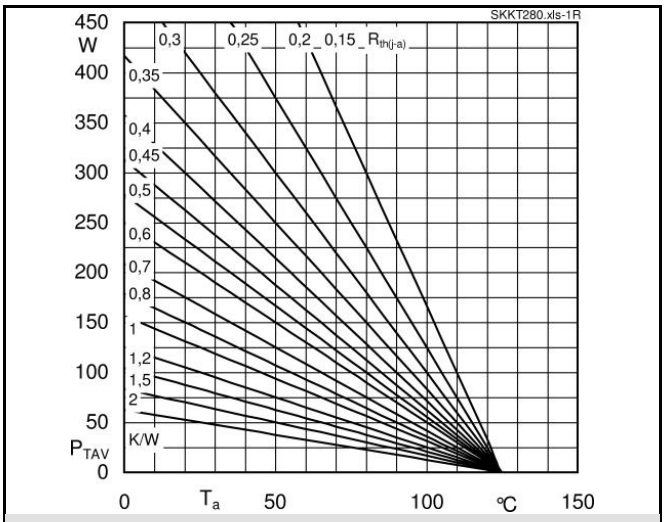


Fig. 1R Power dissipation per thyristor vs. ambient temp.

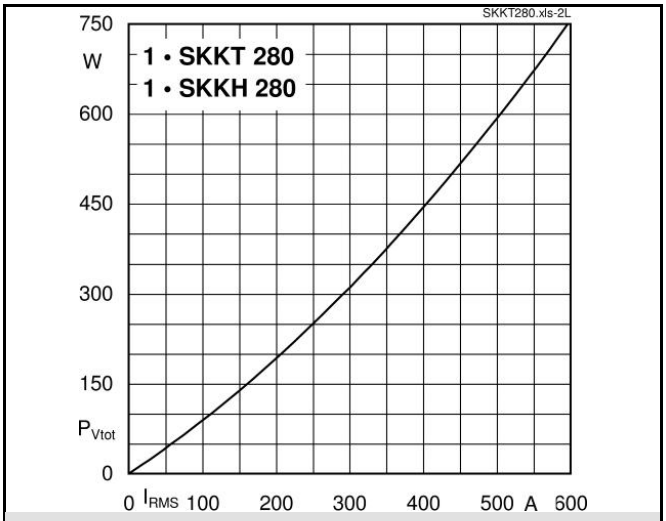


Fig. 2L Power dissipation per module vs. rms current

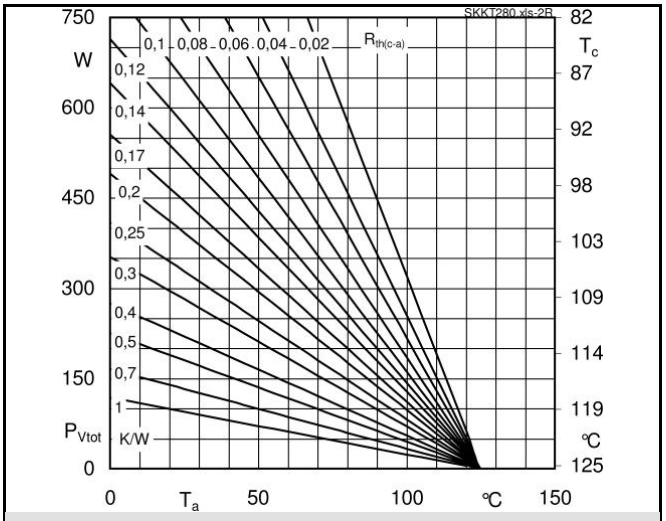


Fig. 2R Power dissipation per module vs. case temp.

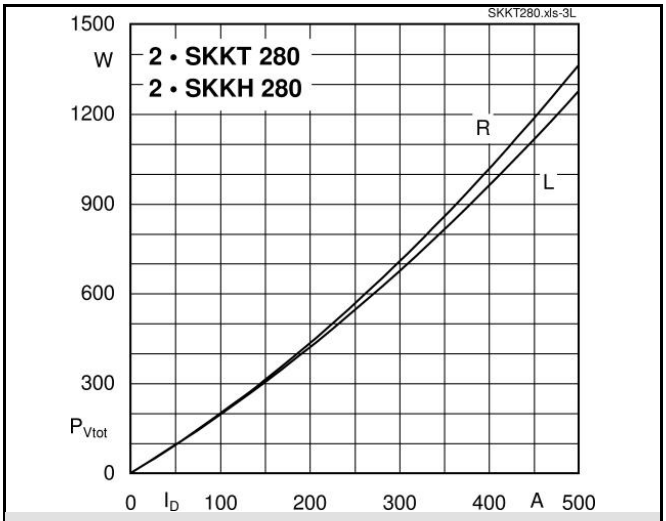


Fig. 3L Power dissipation of two modules vs. direct current

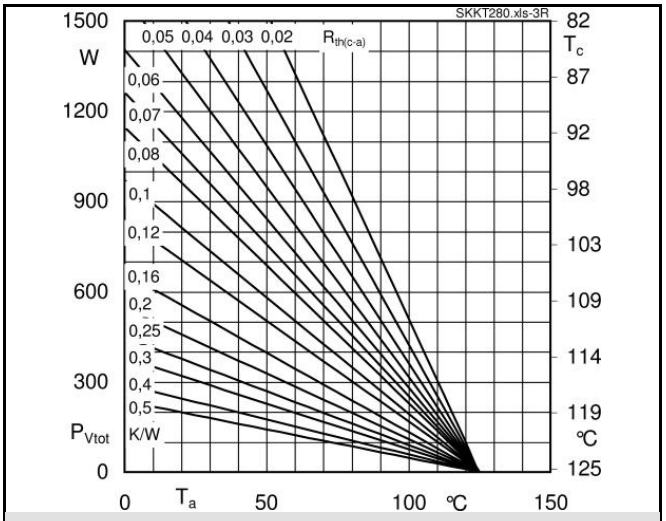


Fig. 3R Power dissipation of two modules vs. case temp.

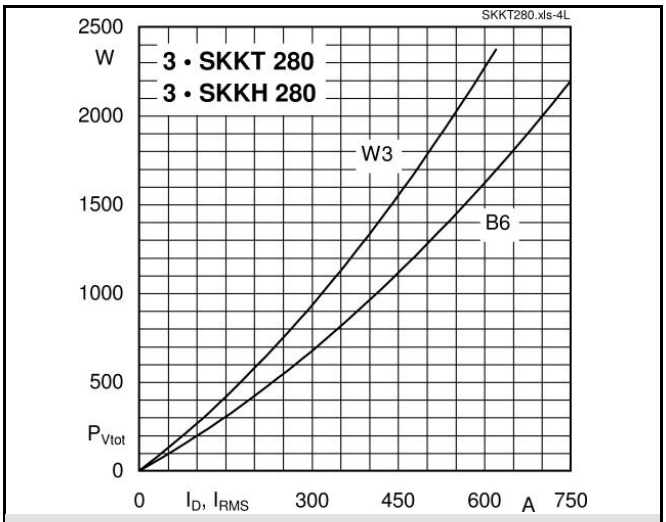


Fig. 4L Power dissipation of three modules vs. direct and rms current

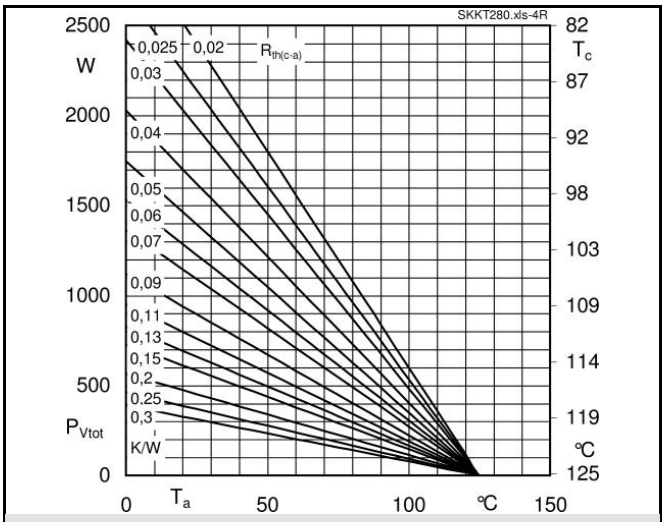


Fig. 4R Power dissipation of three modules vs. case temp.

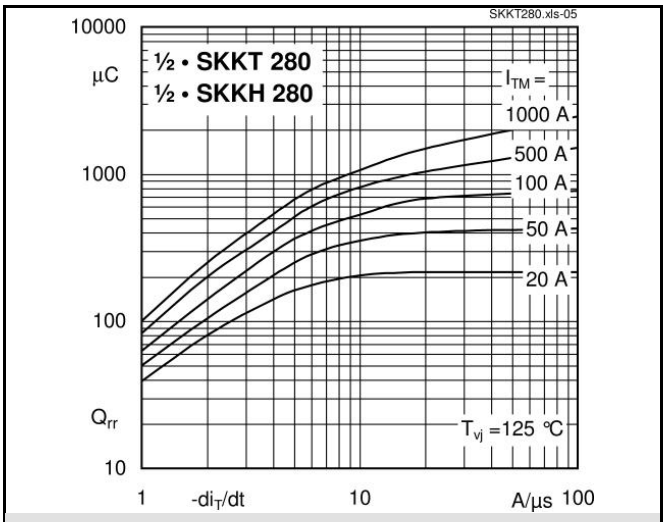


Fig. 5 Recovered charge vs. current decrease

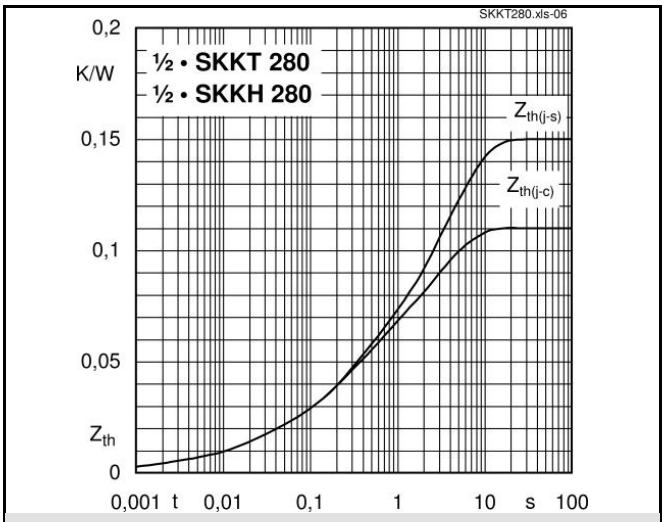


Fig. 6 Transient thermal impedance vs. time

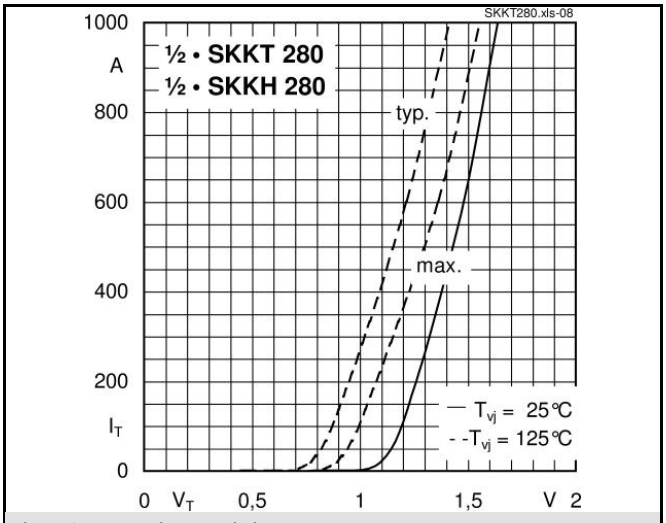


Fig. 7 On-state characteristics

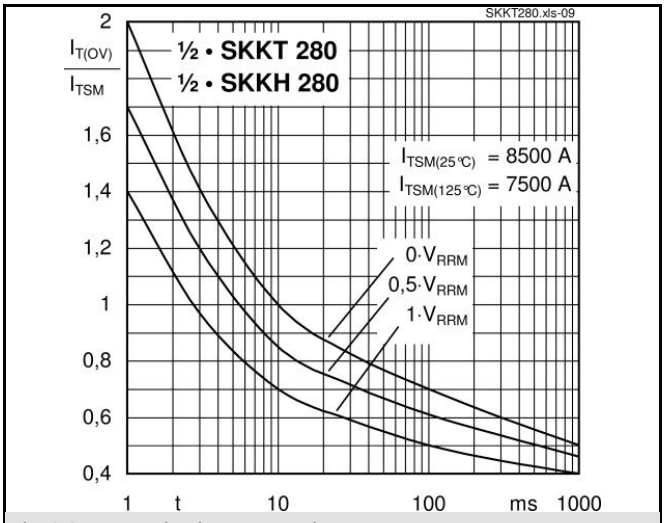


Fig. 8 Surge overload current vs. time

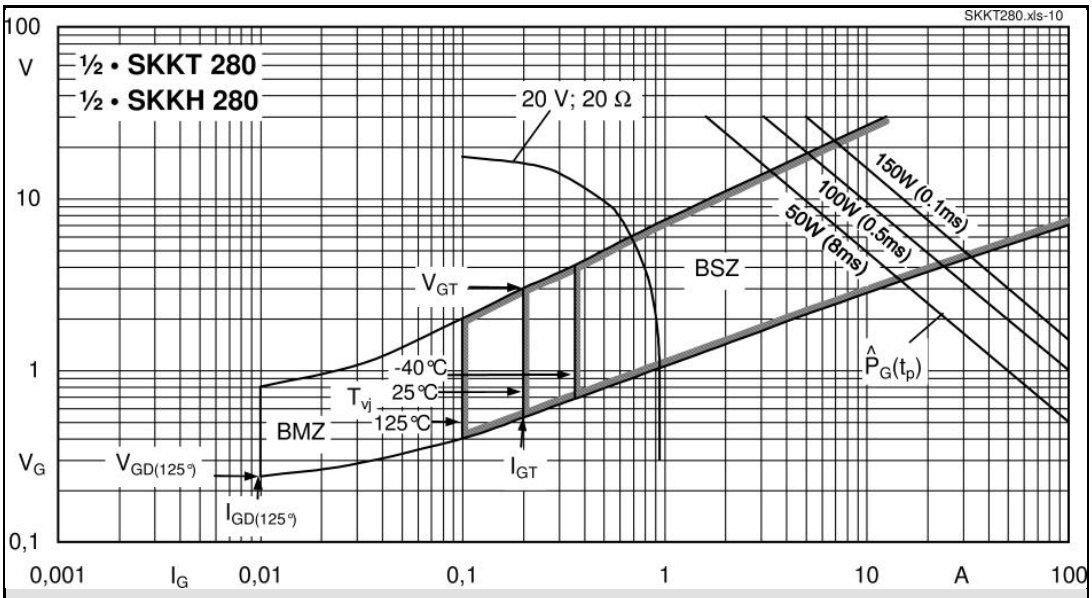
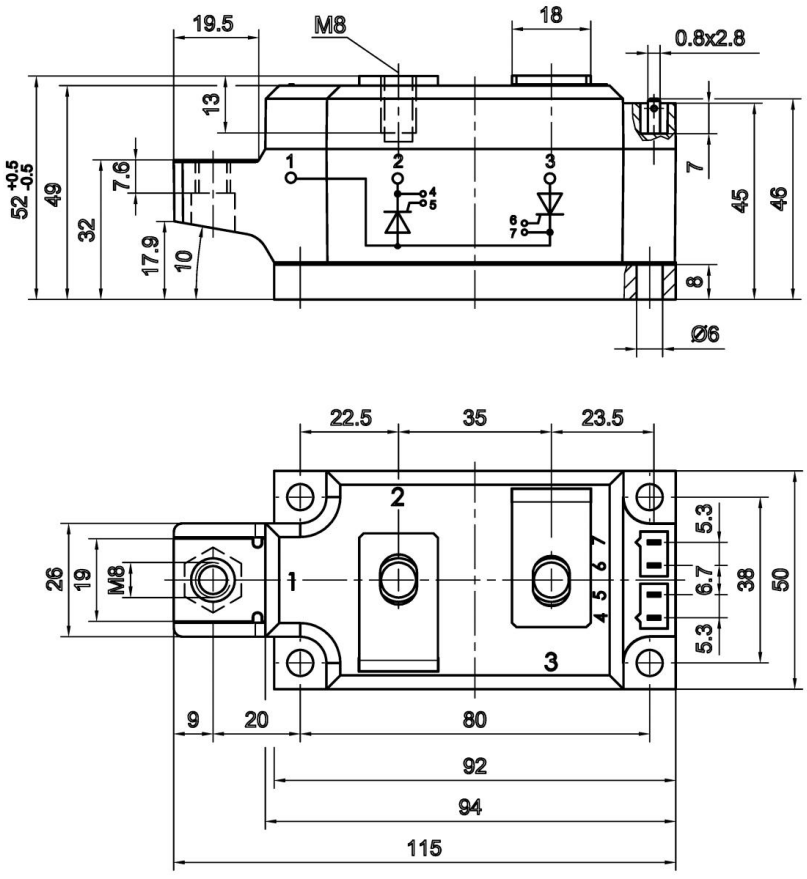
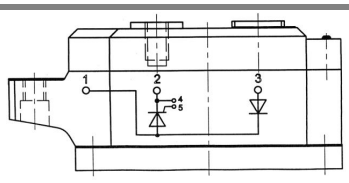


Fig. 9 Gate trigger characteristics

Dimensions in mm



Case A 73b (SKKT)



Case A 76b SKKH

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.